

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
SADAKA, MARIAM G., et al.

Application No.: 10/029093

Filed: December 21, 2001

Docket No.: SC11464ZP

Title: A CHEMISTRY FOR ETCHING QUATERNARY INTERFACE LAYERS ON
InGaAsP MOSTLY FORMED BETWEEN GaAs AND In_xGa(1-x)P LAYERS

§ Patent No.: 6803248
§
§ Issue Date: October 12, 2004
§
§ Examiner: Long Pham
§
§ Group Art Unit: 2814
§
§

Certificate of Submission

I hereby certify that this correspondence is being submitted to
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3-9-07
Date of Submission
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Pat Thomas
Printed Name of Person Signing Certificate

Commissioner for Patents
Alexandria, VA 22313

SUBMISSION OF CERTIFICATE OF CORRECTION

Dear Commissioner:

Enclosed is a Certificate of Correction listing error(s) in the subject patent. Since the errors appear to be on the part of the United States Patent Office, there should be no charge.

Claims 36-42 were added in an Amendment dated January 5, 2004. These additional claims were paid for as evidenced via the Patent Application Fee Determination Record.

2007-03-09
Date

Respectfully submitted,

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**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

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PATENT NO.: 6803248
APPLICATION NO: 10/029093
DATE: 12/12/2004
INVENTOR(S): SADAKA, MARIAM G. et al.

It is certified that error appears in the above-identified patent and that said Letters Patent are hereby corrected as shown below:

After Claim 5, insert dependent claims 36-42 which were added in an Amendment dated January 5, 2004

36. The method of claim 24, wherein the volumetric ratio of H₂O to HCl in the solution is greater than about 15:1.

37. The method of claim 24, wherein the volumetric ratio of H₂O to HCl in the solution is at least about 20:1.

38. The method of claim 36, wherein the mole ratio of H₂O₂ to HCl in the solution is within the range of about 1:12 to about 3:4.

39. The method of claim 36, wherein the mole ratio of H₂O₂ to HCl in the solution is within the range of about 1:12 to about 1:4.

40. The method of claim 37, wherein the mole ratio of H₂O₂ to HCl in the solution is within the range of about 1:12 to about 3:4.

41. The method of claim 37, wherein the mole ratio of H₂O₂ to HCl in the solution is within the range of about 1:12 to about 1:4.

42. The method of claim 29, wherein the composition is selective to InGaP.